RC

FAST RECOVERY 200 NANOSECOND SILICON RECTIFIER

- SMALL SIZE
- LOW LEAKAGE
- HIGH TEMPERATURE STABILITY
- HIGH SURGE CAPABILITY

EDI Type	PRV Volts	Maximum Reverse RECOVERY TIME IN NANOSECONDS (Fig.4)
RC05	50	200
RC10	100	200
RC20	200	200
RC40	400	200
RC60	600	200
RC80	800	200
RC100	1000	200

ELECTRICAL CHARACTERISTICS(at T_A=25°C Unless Otherwise Specified)

Average Rectified Forward Current @ 50°C, I_O	1 Amp
Max. Peak Surge Current , I_{FSM} (8.3 ms)	50 Amp
Max. Forward Voltage Drop @ 1 Amp, V_F	1.4Volts
Max. DC Reverse Current @ PRV and 25 °C, I_R	1 μA
Max. DC Reverse Current @ PRV and100 °C, I_R	50 μA
Trr (Reverse Recovery time), Fig. 4	200 nanosec Max 125nanosec Typical
Ambient Operating Temperature Range, T_A	-55 °C to +150 °C
Storage Temperature Range, T_{STG}	-55 °C to +175 °C

NOTE:
Maxinum lead and terminal temperature for soldering, 3/8 inch from case,5 seconds at 250°C

FIG.1

OUTPUT CURRENT vs AMBIENT TEMPERATURE

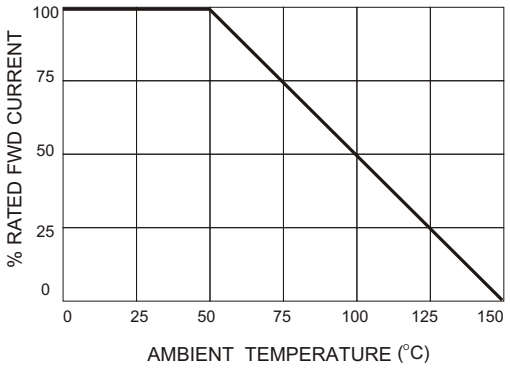


FIG.2

NON-REPETITIVE SURGE CURRENT

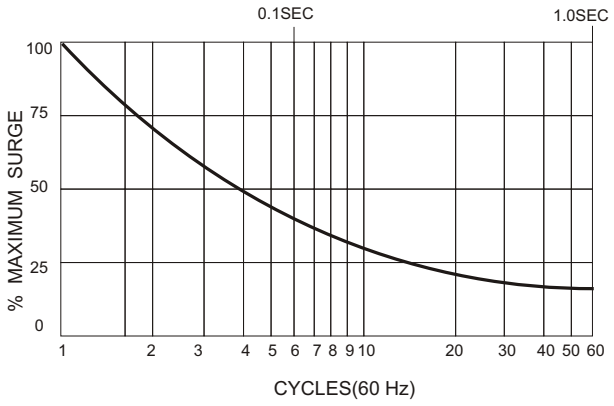
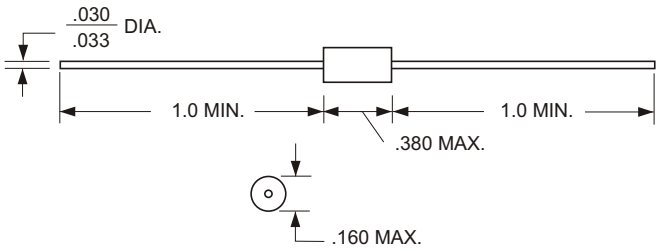


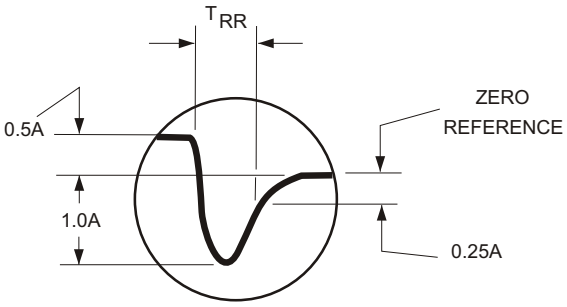
FIG.3

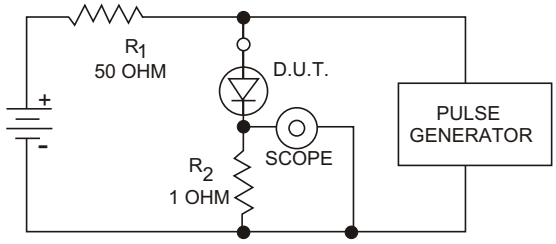


TEST CIRCUIT

FIG.4

TYPICAL REVERSE RECOVERY WAVEFORM





R_1, R_2 NON-INDUCTIVE RESISTORS
PULSE GENERATOR - HEWLETT PACKARD 214A OR EQUIV
I KC REP.RATE, 10μ SEC. PULSE WIDTH
ADJUST PULSE AMPLITUDE FOR PEAK I_R

EDI reserves the right to change these specifications at any time whthout notice.

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